Ref#	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
SI	20	(byoung adj2 ho near3 lim) in:	US-PGPUB; USPAT;	OR	ON	2005/03/28 17:25
S90	2026	(LCD liquid adj crystal) and bond\$3 same substrate and (wash\$3 clean\$3) same substrate and etch\$3 same substrate	EPO; JPO; DERWENT US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ОИ	2005/03/28 17:44
S87	3390	(LCD liquid adj crystal) and bond\$3 same substrate and (wash\$3 clean\$3) and etch\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/28:17:44
S92	111	S91 and (organic BCB PFCB) near2 (insulator insulating protective passivation passivating)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/28 17:45
S91	985	S90 and etch\$3 same (thin thinning)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/28 17:45
S89	164	S88 and (organic BCB PFCB) near2 (insulator insulating protective passivation passivating)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/28 17:45
S88	1426	S87 and etch\$3 same (thin thinning)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/28:17:45
S96	1479	(349/158).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/03/29 15:35
S95	171	(216/23).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO;	OR	OFF	2005/03/29:15:35
S94	767	(216/97).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/03/29 15:35
S93	773	(438/459).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/03/29 15:35
S98	767	(216/97).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/03/29 15:36
S97	262	(216/80).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/03/29 15:36
S99	168	(216/96).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/03/29 15:37
S100	1973	(liquid adj crystal LCD) and etch\$3 same substrate with (clean\$3 wash\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/29 15:38

S102	196	(liquid adj crystal LCD) and etch\$3 same substrate with (clean\$3 wash\$3) same (impurity impurities contaminant)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/29 15:39
S103	78	S102 not S101	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	Й	:2005/03/29:15:51
S101	150	(liquid adj crystal LCD) and etch\$3 same substrate same (impurity impurities contaminant) with (clean\$3 wash\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/29 15:51
S104	764	(216/97):CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO;	OR	OFF	2005/03/29 16:18
S107	6	S106 and (LCD liquid adj crystal)	US-PGPUB; US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/29 16:27
S106	257	(216/80).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO;	OR	OFF	2005/03/29 16:27
S105	23	S104 and (LCD liquid adj crystal)	US-PGPUB; US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/29 16:27
S108	175	S104 and (clean\$3 wash\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT	ÖR	ON	2005/03/29 16:51
S110	257	(216/80).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/03/30 08:44
S109	764	(216/97) CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO;	OR	OFF	2005/03/30 08:44
S111	169	(216/23).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/03/30 08:46
S113	766	(438/459) CCLS.	US-PGPUB, USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/03/30 08:47
S112	26	(S109 S110 S111) and (dry plasma) adj2 etch\$3 same (wash\$3 clean\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/30 08:47
S32		((438/459).CCLS.) and (cleaned cleaning) and (etched etching grinding)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/30 08:47
S114	23	S113 and (dry plasma) adj2 etch\$3 same (wash\$3 clean\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/30 11:22
S115	440	(LCD liquid adj crystal) and (dry plasma) adj2 etch\$3 same (wash\$3 clean\$3) same substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/30 11:39

S116	347	(LCD liquid adj crystal) and (ashing (dry plasma) adj2 etch\$3) with (wash\$3 clean\$3) same substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/30 12:15
S119	19	(ashing (dry plasma) adj2 etch\$3) with (wash\$3 clean\$3) same glass adj2 substrate same (impurity impurities contamination contaminants):	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/30:12:23
S120	59	S118 not (S119 S112)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/30 12:25
S118	76	(LCD liquid adj crystal) and (ashing (dry plasma) adj2 etch\$3) with (wash\$3 clean\$3) same substrate same (impurity impurities contamination contaminants)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/30:12:25